

AMENDMENTS TO THE SPECIFICATION:

Please replace the paragraph beginning on line 23 of page 14 with the following rewritten paragraph:

An alternative recoat method uses a combination of a thin solvent layer and a thicker resist layer to coat the free-standing micromechanical structures. A thin layer of pure solvent such as (PGMEA) or a thin resist is applied to the wafer. This thin layer generally is applied thick enough to cover the structures on the wafer. Excess amounts of the thin layer may be removed by briefly spinning the wafer. Spinning the wafer may help to evenly distribute the solvent layer.

Please replace the paragraph beginning on line 5 of page 15 with the following rewritten paragraph:

A thicker coat of resist is then applied to the wafer. Depending on the structures being coated, a standard resist may be used, or a thicker resist comprising at least 35% dissolved solids solvents, as described above. The thicker layer of resist displaces the thin solvent layer almost instantaneously. The wafer may be spun to remove the excess solvent and resist after the thicker layer of resist has displaced the solvent layer. The thicker resist layer remaining on the wafer may be cured as described above.